

Description

The VSM2301E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

General Features

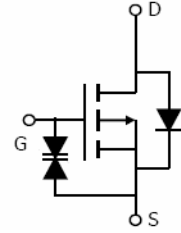
- $V_{DS} = -20V, I_D = -2.6A$
 $R_{DS(ON)} < 150m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 120m\Omega @ V_{GS} = -4.5V$
ESD Rating: 2000V HBM
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Load switch



SOT-23-3



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM2301E-S2	VSM2301E	SOT-23-3	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-2.6	A
Drain Current-Pulsed (Note 1)	I_{DM}	-13	A
Maximum Power Dissipation	P_D	1.0	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	$^\circ C/W$
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Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	0.40	0.7	1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-2A	-	87	120	mΩ
		V _{GS} =-2.5V, I _D =-1A	-	125	150	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-2A	5		-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	325	-	PF
Output Capacitance	C _{OSS}		-	63	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	37	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V,R _L =1. 5Ω V _{GS} =-10V,R _{GEN} =3Ω	-	11		nS
Turn-on Rise Time	t _r		-	5.5		nS
Turn-Off Delay Time	t _{d(off)}		-	22		nS
Turn-Off Fall Time	t _f		-	8		nS
Total Gate Charge	Q _g	V _{DS} =-10V,I _D =-2A, V _{GS} =-4.5V	-	3.2		nC
Gate-Source Charge	Q _{gs}		-	0.6	-	nC
Gate-Drain Charge	Q _{gd}		-	0.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-2.6A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-2.6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

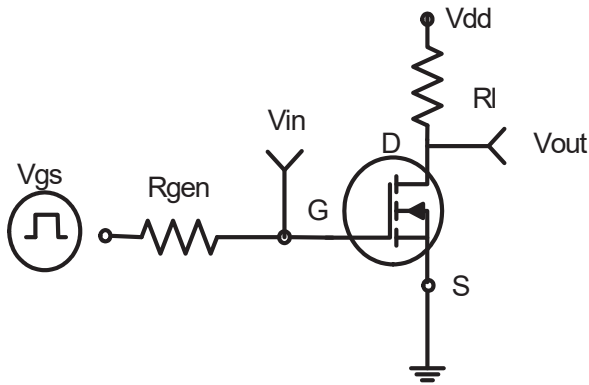


Figure 1: Switching Test Circuit



Figure 2: Switching Waveforms

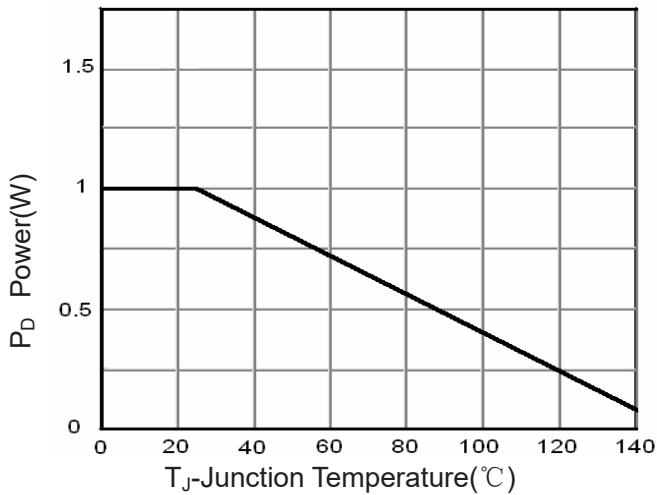


Figure 3 Power Dissipation

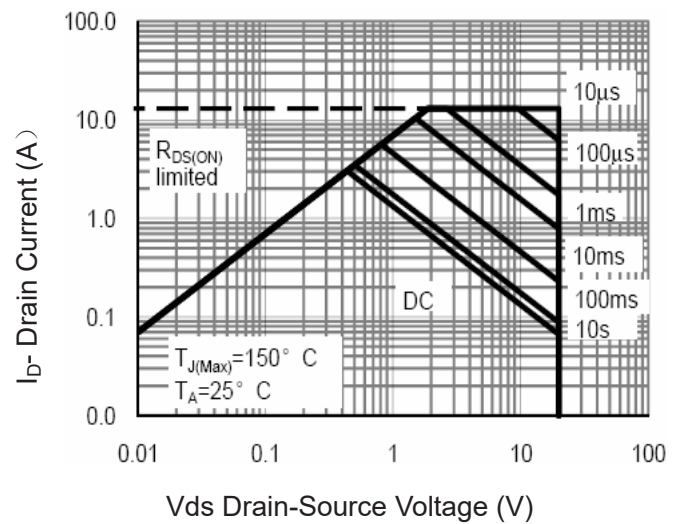


Figure 4 Safe Operation Area

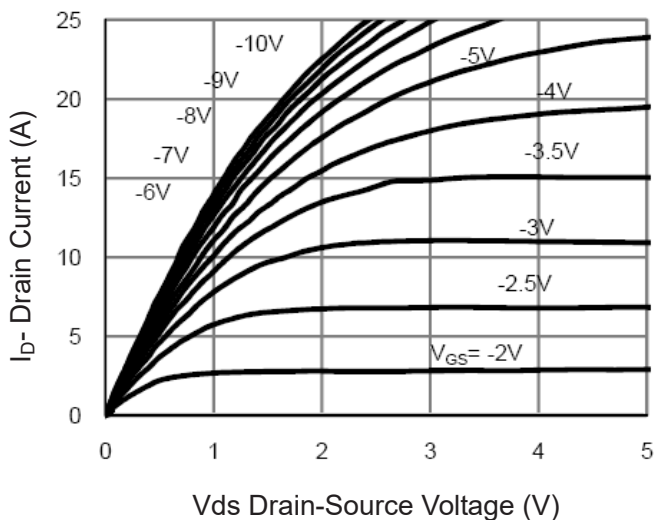


Figure 5 Output Characteristics

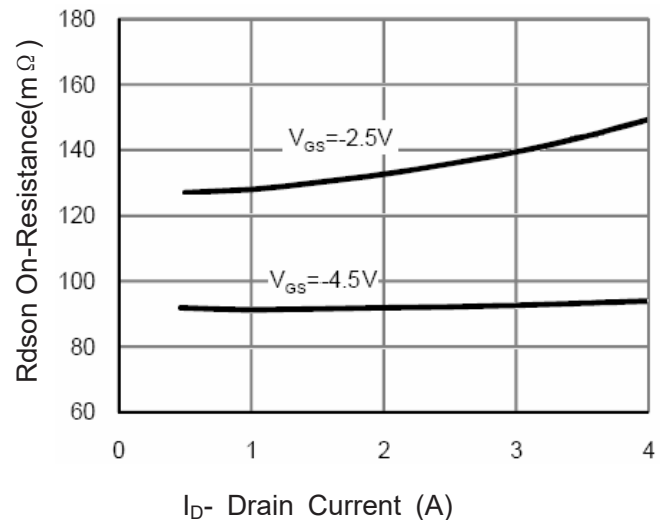
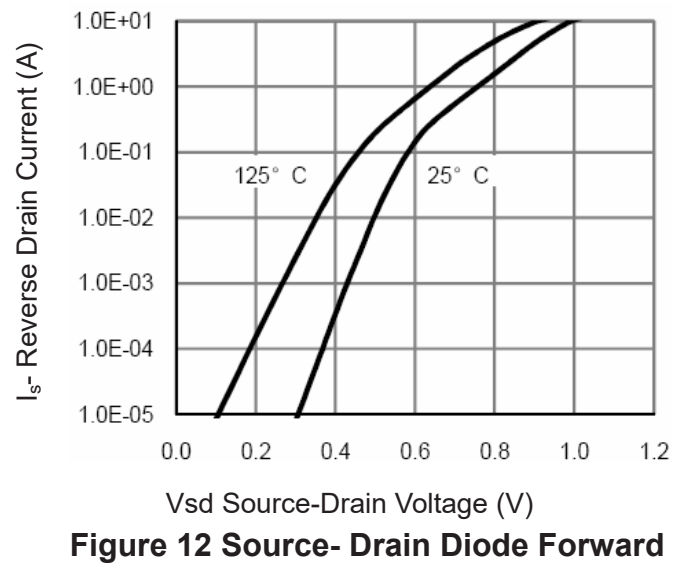
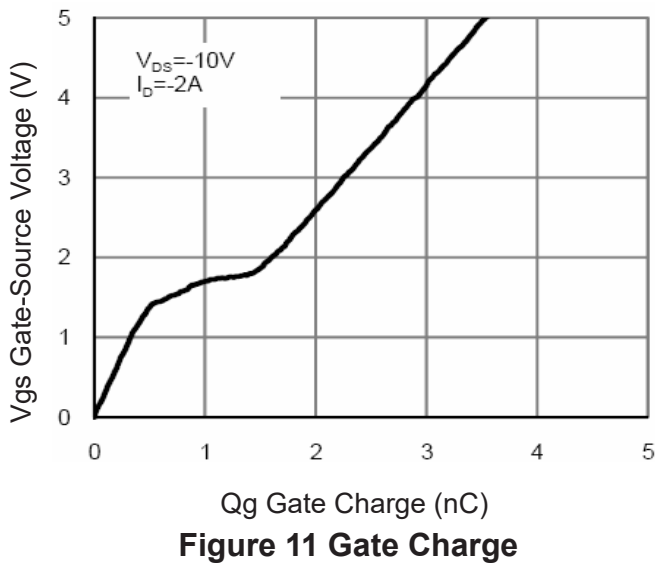
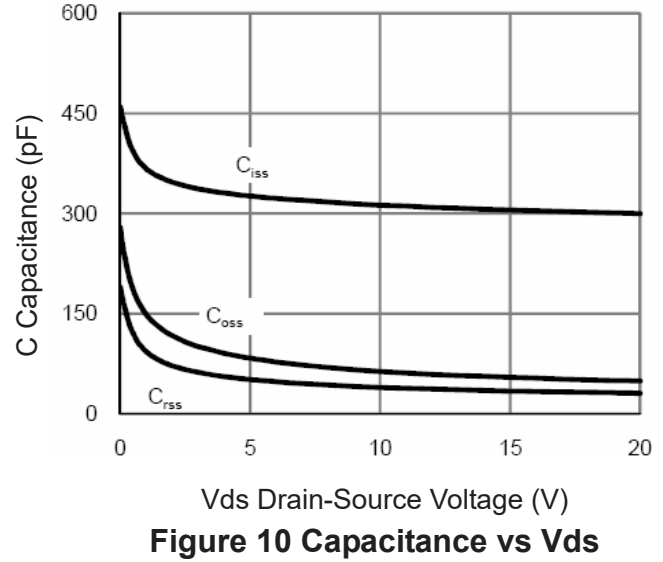
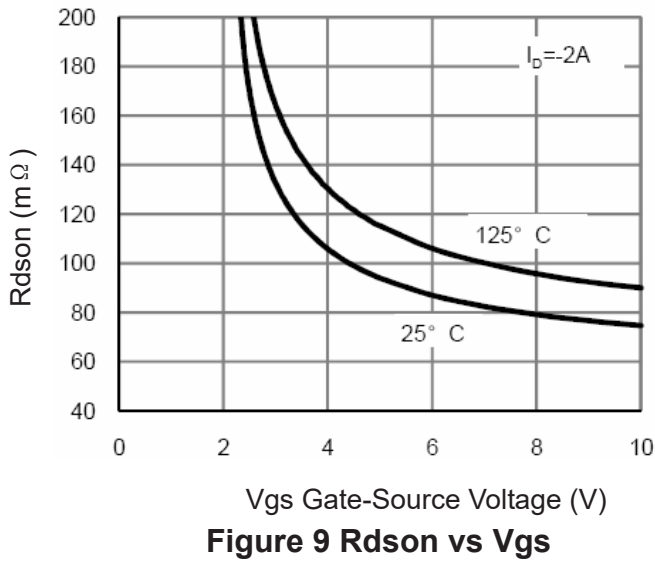
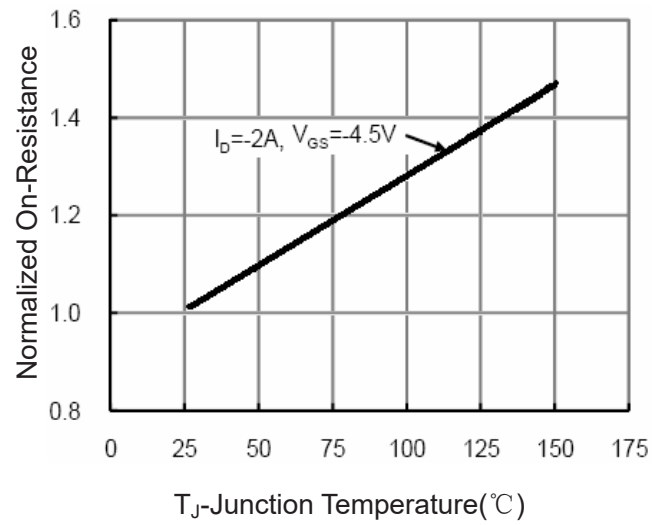
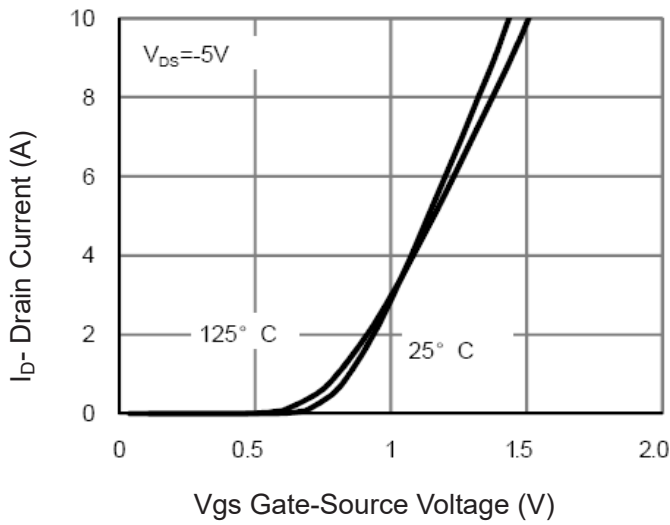


Figure 6 Drain-Source On-Resistance



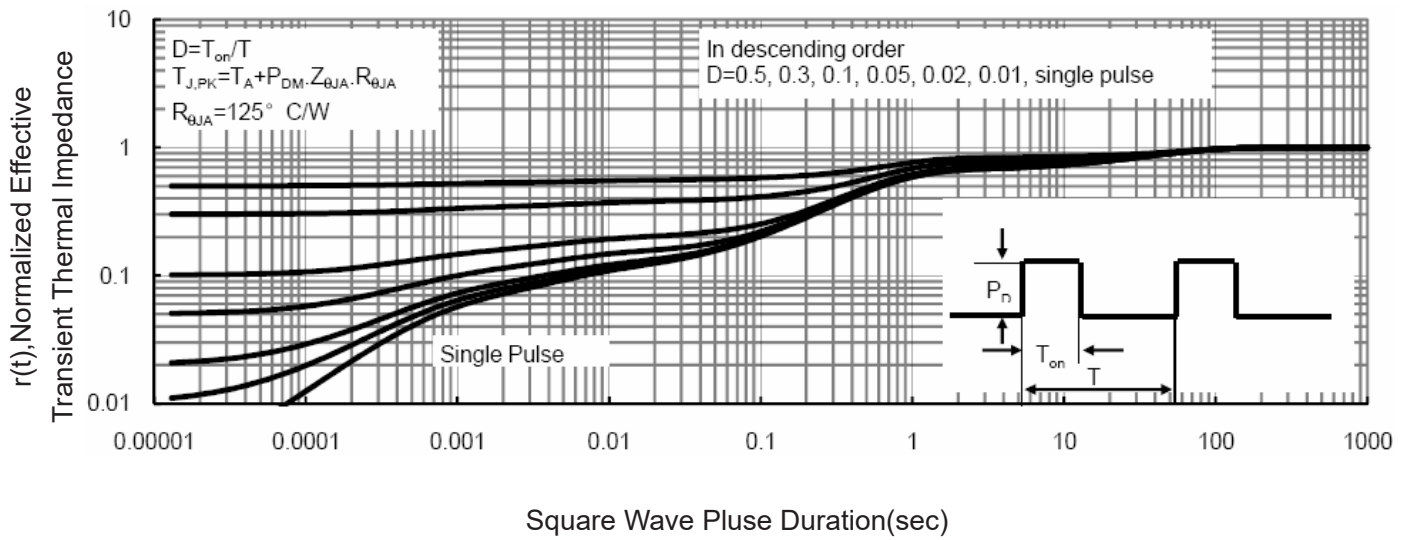


Figure 13 Normalized Maximum Transient Thermal Impedance